

## **Transient Voltage Suppressors for ESD Protection**

### **General Description**

The LESD8D3.3CBT5G is designed to protect voltage sensitive components from ESD and transient voltage events. Excellent clamping capability, low leakage, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium. Because of its small size, it is suitable for use in cellular phones, MP3 players, digital cameras and many other portable applications where board space is at a premium.

### **Applications**

- Cellular phones
- Portable devices
- Digital cameras
- Power supplies

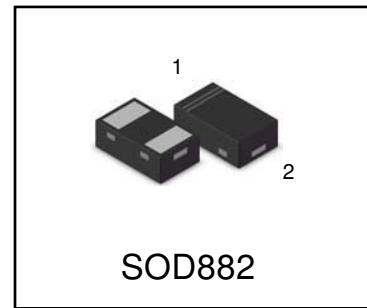
### **Features**

- Small Body Outline Dimensions
- Low Body Height
- Peak Power up to 105 Watts @ 8 x 20 μ s Pulse
- Low Leakage current
- Response Time is Typically < 1 ns
- ESD Rating of Class 3 per Human Body Model

### **Absolute Ratings ( $T_{amb}=25^{\circ}C$ )**

Symbol	Parameter	Value	Units
$P_{PP}$	Peak Pulse Power ( $t_p = 8/20 \mu s$ )	105	W
$T_L$	Maximum lead temperature for soldering during 10s	260	°C
$T_{stg}$	Storage Temperature Range	-55 to +150	°C
$T_{op}$	Operating Temperature Range	-55 to +150	°C
$T_j$	Maximum junction temperature	150	°C
	IEC61000-4-2 (ESD)	air discharge contact discharge	±30 ±30
	IEC61000-4-4 (EFT)	40	KV

### **LESD8D3.3CBT5G**



SOD882



### **Ordering information**

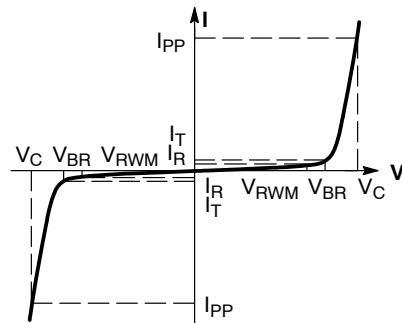
Device	Marking	Shipping
LESD8D3.3CBT5G	DA	10000/Tape&Reel

# LESD8D3.3CBT5G

## Electrical Parameter

( $T_A = 25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter
$I_{PP}$	Maximum Reverse Peak Pulse Current
$V_C$	Clamping Voltage @ $I_{PP}$
$V_{RWM}$	Working Peak Reverse Voltage
$I_R$	Maximum Reverse Leakage Current @ $V_{RWM}$
$V_{BR}$	Breakdown Voltage @ $I_T$
$I_T$	Test Current
$P_{pk}$	Peak Power Dissipation
C	Capacitance @ $V_R = 0$ and $f = 1.0$ MHz



## Electrical Characteristics

Device	$V_{RWM}$ (V)	$I_R$ ( $\mu\text{A}$ ) @ $V_{RWM}$	$V_{BR}$ (V) @ $I_T$ (Note 1)		$I_T$	$V_C$ (V) @ $I_{PP} = 1$ A (Note 2)	$V_C$ (V) @ MAX $I_{PP}$ (Note 2)	$I_{PP}$ (A) (Note 2)	$P_{PK}$ (W) (Note 2)	C (pF)	$R_{DYN}(\Omega)$ @ $t_p=100$ ns(TLP)
	Max	Max	Min	Max		mA	Max				Typ.
LESD8D3.3CBT5G	3.3	0.05	5	6.5	1.0	7	9	10	105	20	0.2

- $V_{BR}$  is measured with a pulse test current  $I_T$  at an ambient temperature of  $25^\circ\text{C}$ .
- Surge current waveform per Figure 1.

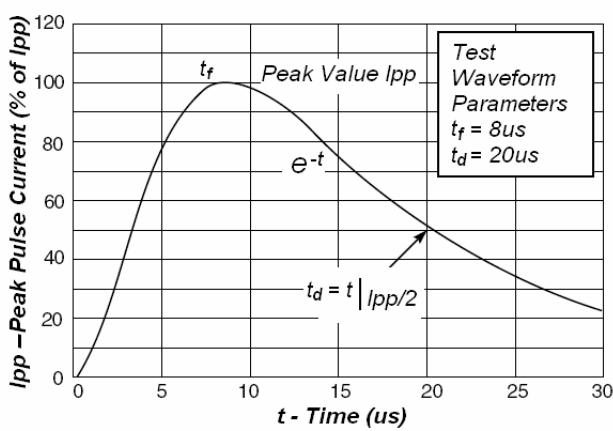


Fig1. Pulse Waveform

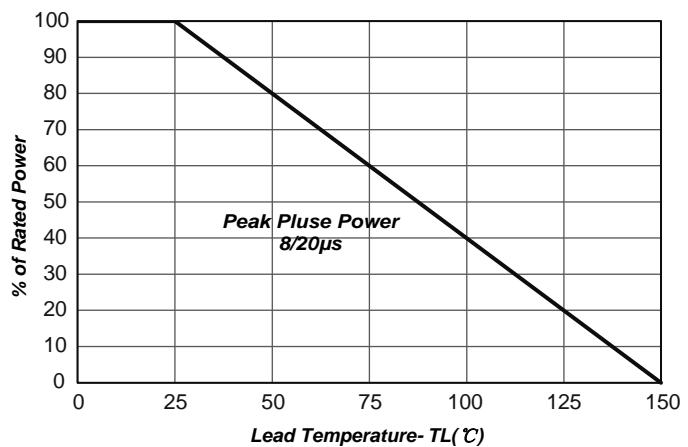
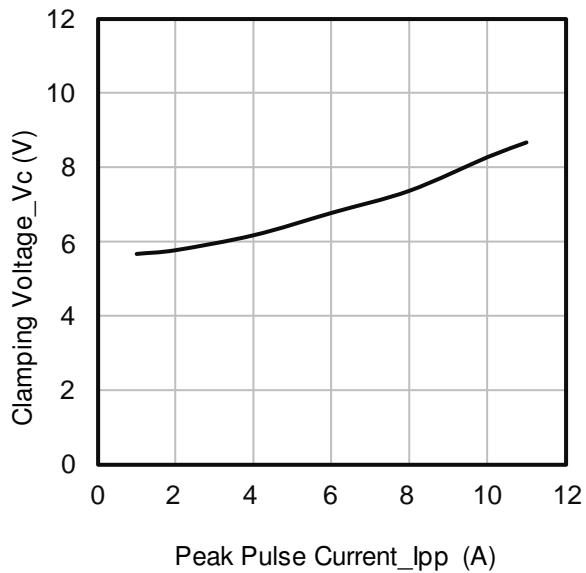
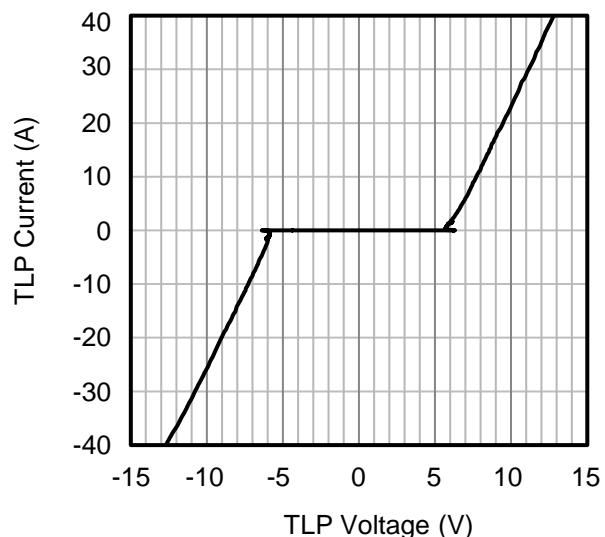


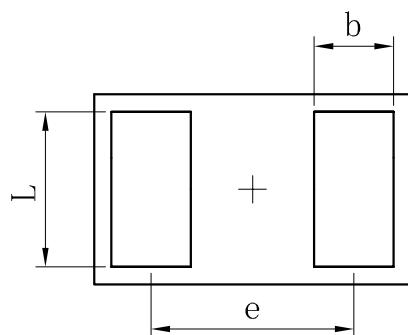
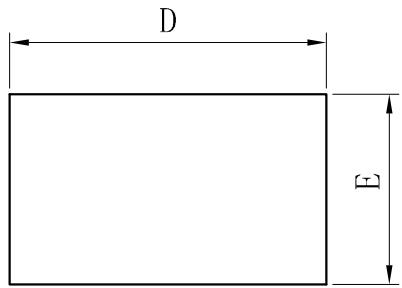
Fig2. Power Derating Curve

**LESD8D3.3CBT5G**

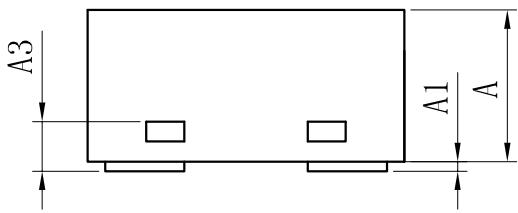
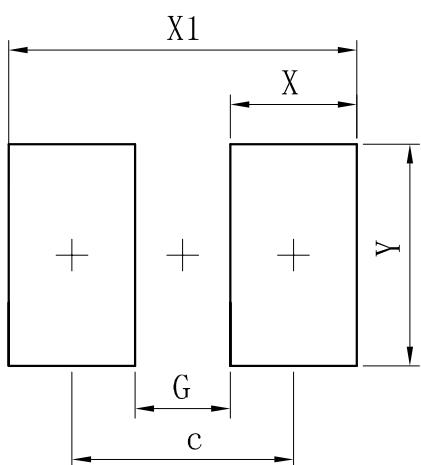
**Fig3. Clamping Voltage vs. Peak Pulse Current**



**Fig4. TLP Measurement**

**OUTLINE AND DIMENSIONS**
**SOD882**


SOD882			
Dim	Min	Typ	Max
D	0.95	1.00	1.05
E	0.55	0.60	0.65
e	-	0.64	-
L	0.44	0.49	0.54
b	0.20	0.25	0.30
A	0.43	0.48	0.53
A1	0	-	0.05
A3	0.127REF.		
All Dimensions in mm			


**SOLDERING FOOTPRINT**
**SOD882**


Dimensions	(mm)
c	0.70
G	0.30
X	0.40
X1	1.10
Y	0.70